

REPLACEMENT CLAIMS

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61. (amended) A method for removing surface contaminants from an air/liquid interface of a semiconductor processing bath for processing semiconductor wafers, said method comprising:

rapidly removing an upper portion of a semiconductor processing fluid present in said bath, while said wafers are in said bath, to permit flow of said upper portion of said processing fluid and thereby break eddy currents holding said surface contaminants at said air/liquid interface.

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65. (amended) A method for removing surface contaminants from an air/liquid interface of a semiconductor processing bath for processing semiconductor wafers, said method comprising:

rapidly removing an upper portion of a semiconductor processing fluid present in said bath by sliding a door located at an upper portion of said bath, while said wafers are in said bath, to permit flow of said upper portion of said processing fluid and thereby break eddy currents holding said surface contaminants at said air/liquid interface.

66. (amended) A method for removing surface contaminants from an air/liquid interface of a semiconductor processing bath for processing semiconductor wafers, said method comprising:

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rapidly removing an upper portion of a semiconductor processing fluid present in said bath by rapidly removing a wafer boat containing said wafers from said bath, while said wafers are in said bath, to permit flow of said upper portion of said processing fluid and thereby break eddy currents holding said surface contaminants at said air/liquid interface.

68. (amended) A method for removing surface contaminants from an air/liquid interface of a semiconductor processing bath for processing semiconductor wafers, said method comprising:

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G'10 } rapidly removing an upper portion of a semiconductor processing fluid present in said bath, while said wafers are in said bath, to permit flow of said upper portion of said processing fluid and thereby break surface tension forces holding said surface contaminants at said air/liquid interface.

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H' 72. (amended) A method for removing surface contaminants from an air/liquid interface of a semiconductor processing bath for processing semiconductor wafers, said method comprising:

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rapidly removing an upper portion of a semiconductor processing fluid present in said bath by sliding a door located at an upper portion of said bath, while said wafers are in said bath, to permit flow of said upper portion of said processing fluid and thereby break surface tension forces holding said surface contaminants at said air/liquid interface.

ju 73. (amended) A method for removing surface contaminants from an air/liquid interface of a semiconductor processing bath for processing semiconductor wafers, said method comprising:

rapidly removing an upper portion of a semiconductor processing fluid present in said bath by rapidly removing a wafer boat containing said wafers from said bath, while said wafers are in said bath, to permit flow of said upper portion of said processing fluid and thereby break surface tension forces holding said surface contaminants at said air/liquid interface.